13003DH

Preliminary

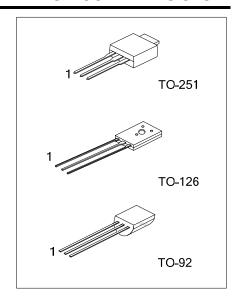
NPN SILICON TRANSISTOR

NPN SILICON BIPOLAR TRANSISTORS FOR LOW FREQUENCY AMPLIFICATION

DESCRIPTION

The UTC 13003DH is a silicon NPN power switching transistor; it uses UTC's advanced technology to provide customers high collector-base breakdown voltage, low reverse leakage current and high reliability, etc.

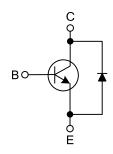
The UTC 13003DH is suitable for electronic ballast power switch circuit and the compact electronic energy-saving light.



FEATURES

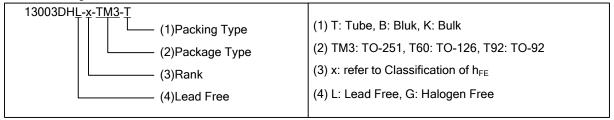
- * High collector-base breakdown voltage
- * Low reverse leakage current
- * High reliability

EQUIVALENT CIRCUIT



ORDERING INFORMATION

Ordering Number		Deelsess	Pin Assignment			Doolsing	
Lead Free	Halogen Free	Package	1	2	3	Packing	
13003DHL-x-TM3-T	13003DHG-x-TM3-T	TO-251	В	C	Е	Tube	
13003DHL-x-T60-K	13003DHG-x-T60-K	TO-126	В	C	Е	Bulk	
13003DHL-x-T92-B	13003DHG-x-T92-B	TO-92	Е	С	В	Tape Box	
13003DHL-x-T92-K	13003DHG-x-T92-K	TO-92	Е	С	В	Bulk	



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■ MARKING INFORMATION

PACKAGE	MARKING		
TO-251	UTC 13003DH P: Halogen Free Lot Code Data Code		
TO-126	UTC DDD Data Code 13003DH L: Lead Free 1 P: Halogen Free		
TO-92	UTC 13003DH L: Lead Free P: Halogen Free Data Code		

■ **ABSOLUTE MAXIMUM RATINGS** (T_A=25°C, unless otherwise noted)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V_{CBO}	600	V
Collector-Emitter Voltage		V_{CEO}	400	V
Emitter-Base Voltage		V_{EBO}	9	V
Continuous Collector Current		I _C	1.8	Α
Danier Diagination	T _A =25°C	1	1.25	W
Power Dissipation	T _C =25°C	P _D	50	W
Junction Temperature		TJ	150	°C
Storage Temperature Range		T _{STG}	-55~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ **ELECTRICAL CHARACTERISTICS** (T_A =25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =0.1mA	600			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =1mA	400			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I _E =0.1mA	9			V
Collector Cut-Off Current	I _{CBO}	V _{CB} =600V, I _E =0			0.1	mA
Collector-Emitter Cut-Off Current	I _{CEO}	V _{CE} =400V, I _B =0			0.1	mA
Emitter-Base Cut-Off Current	I _{EBO}	$V_{EB}=9V$, $I_{C}=0$			0.1	mA
DC Current Gain (Note 1)	h _{FE}	I _C =0.2A, V _{CE} =5.0V	15		30	
Low ourrent and high ourrent has be ratio	h /h	h _{FE1} : V _{CE} =5V, I _C =5mA	0.75	0.9		
Low current and high current h _{FE2} h _{FE1} ratio	h _{FE1} / h _{FE2}	h _{FE2} : V _{CE} =5V, I _C =0.2A		0.9		
Collector-Emitter Saturation Voltage (Note)	$V_{CE(SAT)}$	I _C =1A, I _B =0.25A		0.30	0.8	V
Base-Emitter Saturation Voltage (Note)	$V_{BE(SAT)}$	I _C =1A, I _B =0.25A		0.9	1.2	V
Storage Time	t _S		3		5	μs
Rise Time	t_R	UI9600, I _C =0.1A			1	μs
Fall Time	t_{F}	1			1	μs
Transition Frequency	f_T	I _C =0.1A, V _{CE} =10V, f=1MHz	5			MHz
Diode Forward Voltage	V_{F}	I _F =1.5A			2.5	V

Note: Pulse test, pulse width tp≤300µs, Duty cycle≤2%

■ CLASSIFICATION OF h_{FE}

RANK	A	В	С		
RANGE	15 ~ 20	20 ~ 25	25 ~ 30		

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